

Amendments to the Claims

Claims 1-59 (Canceled).

60. (Previously Presented): A method of forming a capacitor comprising:

forming a first capacitor electrode over a substrate;

forming a substantially crystalline capacitor dielectric layer over the first capacitor electrode;

providing the substrate with substantially crystalline capacitor dielectric layer within a chemical vapor deposition reactor; and

feeding a gaseous precursor comprising silicon to the chemical vapor deposition reactor under conditions effective to substantially selectively deposit polysilicon on the substantially crystalline capacitor dielectric layer and not on exposed substantially amorphous material, and forming the polysilicon into a second capacitor electrode.

61. (Original): The method of claim 60 wherein the conditions comprise pressure greater than 30 mTorr and temperature of less than 800°C.

62. (Previously Presented): The method of claim 60 wherein the conditions are void of feeding chlorine containing gas to the chemical vapor deposition reactor.

63. (Original): The method of claim 60 wherein the crystalline capacitor dielectric layer comprises barium strontium titanate.

64. (Original): The method of claim 60 wherein the crystalline capacitor dielectric layer comprises Ta_2O_5 .

65. (Previously Presented): The method of claim 60 wherein the gaseous precursor comprising silicon comprises a silane.

66. (Currently Amended): The method of ~~claim 60~~ claim 65 wherein the gaseous precursor comprises a chlorosilane.

67. (Previously Presented): The method of claim 60 wherein the gaseous precursor comprising silicon comprises a silane, and the conditions include a chemical vapor deposition reactor atmosphere during depositing consisting essentially of gaseous silane precursor.

68. (Previously Presented): The method of claim 60 wherein the conditions comprise temperature of less than 800°C and pressure greater than 30 mTorr, and wherein the gaseous precursor comprising silicon comprises a silane, and the conditions include a chemical vapor deposition reactor atmosphere during depositing consisting essentially of the silane.

69. (Previously Presented): The method of claim 60 wherein the conditions comprise pressure greater than 30 mTorr.

70. (Previously Presented): The method of claim 60 wherein the conditions are void of plasma.

71. (Previously Presented): The method of claim 60 wherein the conditions are substantially void of gas comprising a conductivity enhancing dopant.

72. (Previously Presented): The method of claim 60 wherein the conditions comprise a gas comprising a conductivity enhancing dopant.

73. (Previously Presented): The method of claim 60 wherein the conditions comprise temperature of greater than or equal to about 650°C.

74. (Previously Presented): The method of claim 60 wherein the conditions comprise pressure less than or equal to about 100 mTorr.

75. (Previously Presented): The method of claim 60 wherein the conditions comprise a temperature of from about 650°C to about 850°C and a chemical vapor deposition reactor pressure at less than or equal to about 100 mTorr.

76. (Previously Presented): The method of claim 60 wherein the exposed substantially amorphous material comprises SiO₂.